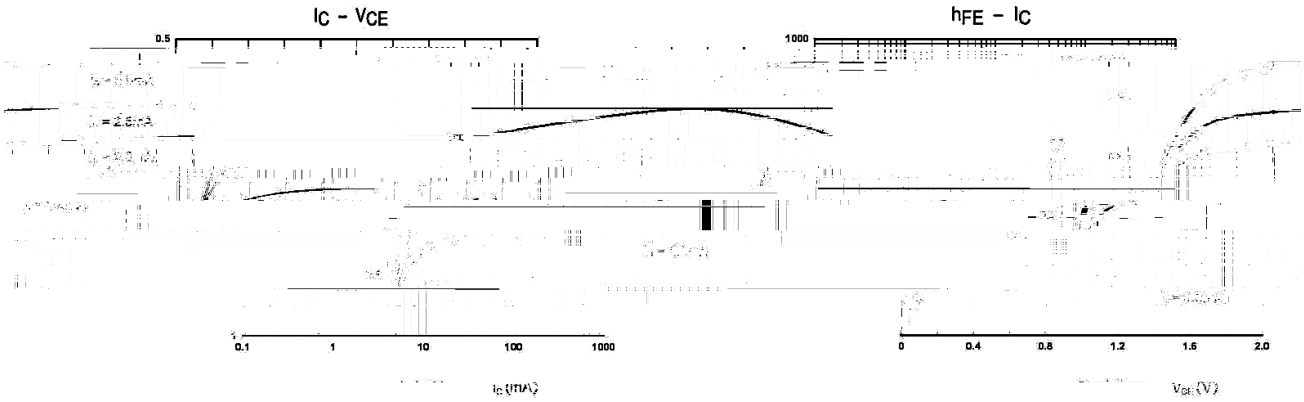
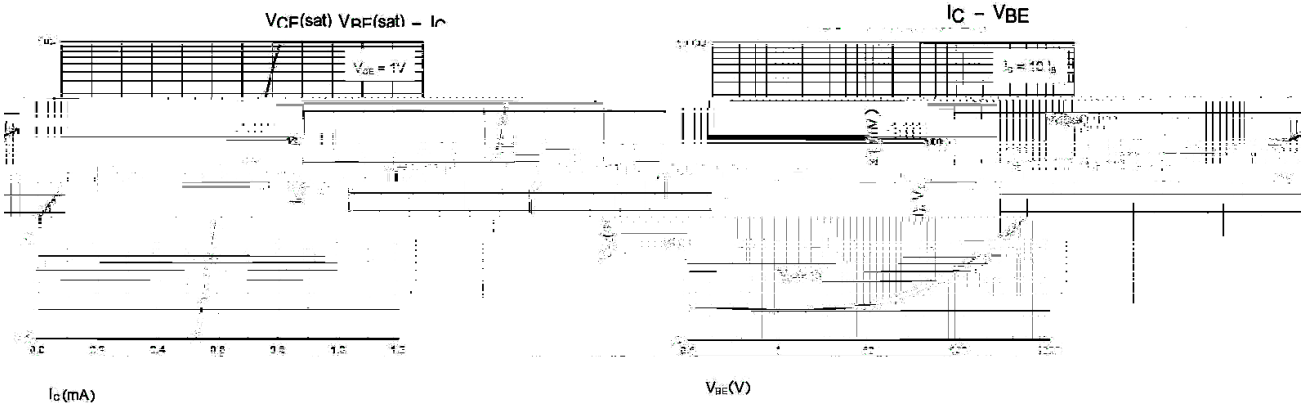
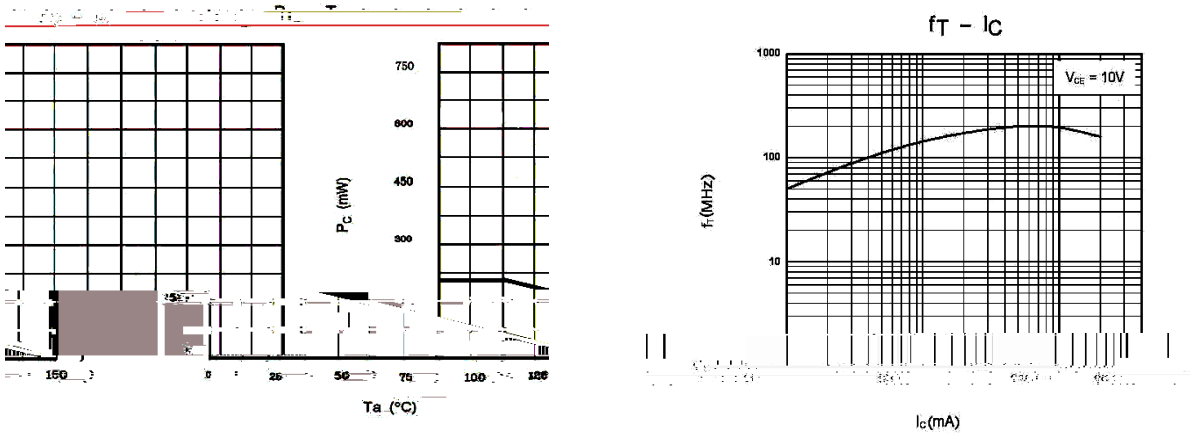
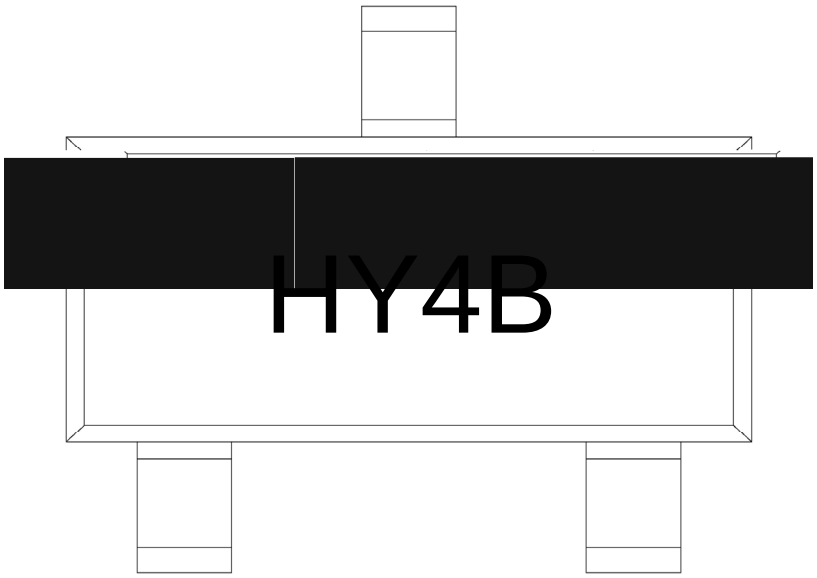
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-40	V
Collector to Emitter Voltage	V_{CEO}	-25	V
Emitter to Base Voltage	V_{EBO}	-6.0	V
Collector Current	I_C	-800	mA
Base Current	I_B	-200	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-65 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=-0.1mA I_E=0	-40			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=-2.0mA I_B=0	-25			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=-0.1mA I_C=0	-6.0			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=-35V I_E=0			-0.1	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=-6.0V I_C=0			-0.1	μA
DC Current Gain	$h_{FE(1)}$	V_{CE}=-1.0V I_C=-100mA	85		300	
	$h_{FE(2)}$	V_{CE}=-1.0V I_C=-500mA	40			
	$h_{FE(3)}$	V_{CE}=-1.0V I_C=-5.0mA	45			
Collector-emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-500mA I_B=-50mA		-0.28	-0.6	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=-500mA I_B=-50mA		-0.98	-1.2	V
Base-Emitter Voltage	V_{BE}	V_{CE}=-1.0V I_C=-10mA		-0.66	-1.0	V
Transition Frequency	f_T	V_{CE}=-10V I_C=-50mA	100	200		MHz
Collector Output Capacitance	C_{ob}	V_{CB}=-10V I_E=0 f=1.0MHz		15		pF


IC – VCE
0.5
0.1
1
10
100
1000
IC (mA)
hFE – IC
1000
0
0.4
0.8
1.2
1.6
2.0
VCE (V)


VCE(sat) VBE(sat) – IC
VCE = 1V
IC (mA)
IC – VBE
IB = 10 IB
VBE (V)


750
600
450
300
PC (mW)
150
0
25
50
75
100
125
Ta (°C)
fT – IC
1000
100
10
VCE = 10V
fT (MHz)
IC (mA)



H

Y4

B h_{FE}

Note:

H	Company Code
Y4	Product Type Code
B	h_{FE} Classifications Symbol Code

Temperature Profile for IR Reflow Soldering(Pb-Free)

			Note:
1	150 180	60 90sec;	1.Preheating:150~180 , Time:60~90sec.
2	245±5	5±0.5sec;	2.Peak Temp.:245±5 , Duration:5±0.5sec.
3		2 10 /sec.	3. Cooling Speed: 2~10 /sec.

260±5	10±1 sec.	Temp.:260±5	Time:10±1 sec

/ REEL

Package Type	Units					Dimension (unit mm³)		
	Units/Reel /	Reels/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Reel	Inner Box	Outer Box